

Please replace the sentence beginning on page 4, line 31, with the following rewritten sentence:

-- The higher temperature heat treatment results in the bonding of surface 104 to wafer 401 at the SiO₂ interface 601.--

Please replace the paragraph on page 5, line 14, with the following rewritten paragraph:

-- In one embodiment where there is no implanting step (i.e., hydrogen implant), the embrittled region is not formed. The strained silicon layer 104 is transferred to the SOI wafer 401 by a bonded-etchback process on the silicon wafer 101 and the strained SiGe 104. this gives the strained silicon film on the SOI wafer 401.--

IN THE CLAIMS

Following is a complete set of claims as amended with this response, which includes amendments to claims 14-19, and adds new claims 20-33.

CLEAN VERSION OF THE ENTIRE SET OF CLAIMS

What is claimed is:

1 14. (AMENDED) A device comprising:
2 a silicon layer;
3 a relaxed layer; and
4 a strained silicon layer in contact with the relaxed layer, the strained silicon layer to
5 be transferred to top of a wafer by a heat treatment, the wafer having a base substrate and
6 an oxidized film.

1 15. (AMENDED) The device of claim 14 further comprising an embrittled
2 region.